

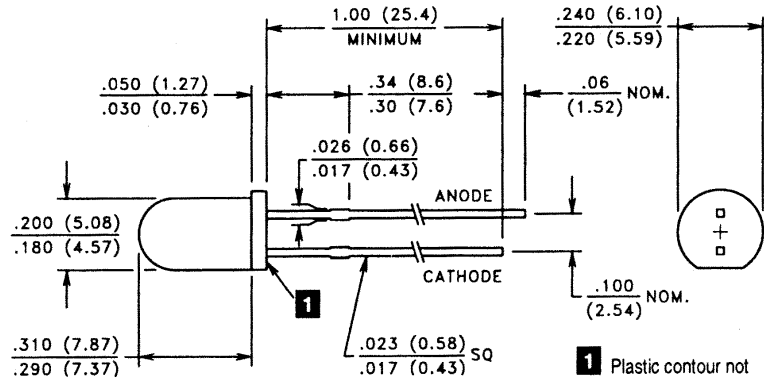
# GaAlAs Infrared Emitting Diodes

T-1<sup>3/4</sup> (5 mm) Plastic Package — 880 nm

## VTE1261H, 1262H



### PACKAGE DIMENSIONS inch (mm)



CASE 26 T-1<sup>3/4</sup> (5 mm)  
CHIP SIZE: .018" x .018"

### DESCRIPTION

This narrow beam angle 5 mm diameter plastic packaged emitter contains a large area, double wirebonded, GaAlAs, 880 nm, high efficiency IRED chip suitable for higher current pulse applications.

### RoHS Compliant



### ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Voltage:	5.0V
Storage and Operating:	-40°C to 100°C	Maximum Reverse Current @ V <sub>R</sub> = 5V:	10 μA
Continuous Power Dissipation:	200 mW	Peak Wavelength (Typical):	880 nm
Derate above 30°C:	2.86 mW/°C	Junction Capacitance @ 0V, 1 MHz (Typ.):	35 pF
Maximum Continuous Current:	100 mA	Response Time @ I <sub>F</sub> = 20 mA	
Derate above 30°C:	1.43 mA/°C	Rise: 1.0 μs Fall: 1.0 μs	
Peak Forward Current, 10 μs, 100 pps:	3.0 A	Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	-8%/°C	(1.6 mm from case, 5 seconds max.)	

### ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle Typ.	
	Irradiance				Radiant Intensity	Total Power	Test Current	V <sub>F</sub>		
	E <sub>e</sub>		Condition		I <sub>e</sub>	P <sub>O</sub>	I <sub>FT</sub>	@ I <sub>FT</sub>		
	mW/cm <sup>2</sup>		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.		Max.
VTE1261H	3.0	3.9	36	6.4	39	20	100	1.5	2.0	±10°
VTE1262H	4.0	5.2	36	6.4	52	25	100	1.5	2.0	±10°

■ Refer to General Product Notes, page 2.